What is claim d is:

1. A semiconductor device production apparatus comprising:

a rotary table section including a rotary table for supporting a wafer thereon;

a chamber for housing the rotary table section;

a heater provided in the chamber for heating the wafer;

a temperature sensing device for sensing a temperature of the wafer;

a temperature measuring section for converting the sensed temperature into a first signal to output the first signal; and

a signal generating section for converting the output first signal into a second signal detectable from outside the chamber;

wherein the temperature sensing device, the temperature measuring section and the signal generating section are attached to the rotary table section.

2. A semiconductor device production apparatus as set forth in claim 1, wherein the temperature sensing device includes a thermocouple.

3. A semiconductor device production apparatus as set forth in claim 1, wherein the signal generating section comprises a detachable storage device for converting the first signal into a storage data to store the storage data as the second signal.

4. A semiconductor device production apparatus as set forth in claim 1, wherein the signal generating section comprises a wireless transmitter for converting the first signal into a wireless

signal to transmit the wireless signal as the second signal.

5. A semiconductor device production apparatus as set forth in claim 1, wherein the signal generating section comprises a display device for converting the first signal into display data to display the display data as the second signal.

6. A semiconductor device production apparatus as set forth in claim 3, further comprising a storage data reader for read out the storage data from the storage device and a heater controlling section for controlling the heater on the basis of the read out storage data, the storage data reader and the heater controlling section being provided outside the chamber.

7. A semiconductor device production apparatus as set forth in claim 4, further comprising a receiver for receiving the wireless signal from the transmitter, and a heater controlling section for controlling the heater on the basis of the received signal, the receiver and the heater controlling section being provided outside the chamber.

8. A semiconductor device production method comprising the steps of:

providing a semiconductor device production apparatus as recited in claim 1;

placing a wafer on the rotary table;

heating the wafer by the heater;

supplying a material gas into the chamber;

detecting the second signal outside the chamber; and

controlling the heater on the basis of the detected second signal for production of a semiconductor device.